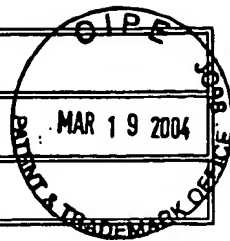
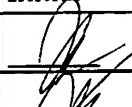
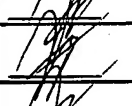
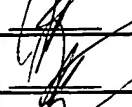
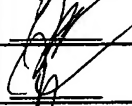
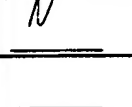
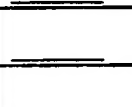
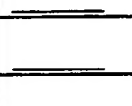


INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970607B	Serial No. 10/050,169
	Applicant(s): Shinichiroh IKEMASU et al.	
	Filing Date: January 18, 2002	Group Art Unit: 2814



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